

NDF03N60Z, NDD03N60Z

N-Channel Power MOSFET 600 V, 3.6 Ω

Features

- Low ON Resistance
- Low Gate Charge
- ESD Diode–Protected Gate
- 100% Avalanche Tested
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

ABSOLUTE MAXIMUM RATINGS (T_C = 25°C unless otherwise noted)

Rating	Symbol	NDF	NDD	Unit
Drain–to–Source Voltage	V _{DSS}	600		V
Continuous Drain Current R _{θJC}	I _D	3.1 (Note 1)	2.6	A
Continuous Drain Current R _{θJC} T _A = 100°C	I _D	2.9 (Note 1)	1.65	A
Pulsed Drain Current, V _{GS} @ 10 V	I _{DM}	12	10	A
Power Dissipation R _{θJC}	P _D	27	61	W
Gate–to–Source Voltage	V _{GS}	±30		V
Single Pulse Avalanche Energy, I _D = 3.0 A	E _{AS}	100		mJ
ESD (HBM) (JESD 22–A114)	V _{esd}	3000		V
RMS Isolation Voltage (t = 0.3 sec., R.H. ≤ 30%, T _A = 25°C) (Figure 17)	V _{ISO}	4500		V
Peak Diode Recovery (Note 2)	dv/dt	4.5		V/ns
Continuous Source Current (Body Diode)	I _S	3.0		A
Maximum Temperature for Soldering Leads	T _L	260		°C
Operating Junction and Storage Temperature Range	T _J , T _{stg}	–55 to 150		°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

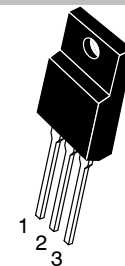
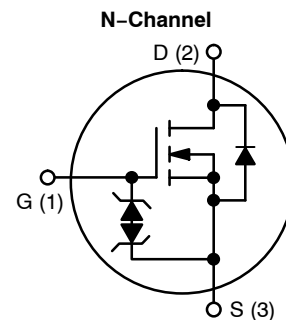
1. Limited by maximum junction temperature
2. I_{SD} = 3.0 A, di/dt ≤ 100 A/μs, V_{DD} ≤ BV_{DSS}, T_J = +150°C



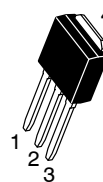
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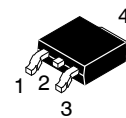
V _{DSS}	R _{DS(on)} (MAX) @ 1.2 A
600 V	3.6 Ω



NDF03N60ZG,
NDF03N60ZH
TO-220FP
CASE 221AH



NDD03N60Z-1G
IPAK
CASE 369D



NDD03N60ZT4G
DPAK
CASE 369AA

MARKING AND ORDERING INFORMATION

See detailed ordering and shipping information on page 7 of this data sheet.

NDF03N60Z, NDD03N60Z

THERMAL RESISTANCE

Parameter	Symbol	Value	Unit	
Junction-to-Case (Drain)	$R_{\theta JC}$	NDF03N60Z NDD03N60Z	4.7 2.0	°C/W
Junction-to-Ambient Steady State		(Note 3) NDF03N60Z (Note 4) NDD03N60Z (Note 3) NDD03N60Z-1	51 40 80	

3. Insertion mounted

4. Surface mounted on FR4 board using 1" sq. pad size, (Cu area = 1.127 in sq [2 oz] including traces).

ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Test Conditions	Symbol	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 1\text{ mA}$	BV_{DSS}	600			V
Breakdown Voltage Temperature Co-efficient	Reference to 25°C , $I_D = 1\text{ mA}$	$\Delta BV_{DSS}/\Delta T_J$		0.6		V/°C
Drain-to-Source Leakage Current	$V_{DS} = 600\text{ V}, V_{GS} = 0\text{ V}$	I_{DSS}	25°C		1	μA
			150°C		50	
Gate-to-Source Forward Leakage	$V_{GS} = \pm 20\text{ V}$	I_{GSS}			±10	μA

ON CHARACTERISTICS (Note 5)

Static Drain-to-Source On-Resistance	$V_{GS} = 10\text{ V}, I_D = 1.2\text{ A}$	$R_{DS(on)}$		3.3	3.6	Ω
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 50\text{ μA}$	$V_{GS(th)}$	3.0	3.9	4.5	V
Forward Transconductance	$V_{DS} = 15\text{ V}, I_D = 1.5\text{ A}$	g_{FS}		2.0		S

DYNAMIC CHARACTERISTICS

Input Capacitance (Note 6)	$V_{DS} = 25\text{ V}, V_{GS} = 0\text{ V},$ $f = 1.0\text{ MHz}$	C_{iss}	248	312	372	pF
Output Capacitance (Note 6)		C_{oss}	30	39	50	
Reverse Transfer Capacitance (Note 6)		C_{rss}	4	8	12	
Total Gate Charge (Note 6)	$V_{DD} = 300\text{ V}, I_D = 3.0\text{ A},$ $V_{GS} = 10\text{ V}$	Q_g	6	12	18	nC
Gate-to-Source Charge (Note 6)		Q_{gs}	1.5	2.5	4	
Gate-to-Drain ("Miller") Charge (Note 6)		Q_{gd}	3	6.1	9	
Plateau Voltage		V_{GP}		6.4		
Gate Resistance		R_g		6.0		Ω

RESISTIVE SWITCHING CHARACTERISTICS

Turn-On Delay Time	$V_{DD} = 300\text{ V}, I_D = 3.0\text{ A},$ $V_{GS} = 10\text{ V}, R_G = 5\text{ Ω}$	$t_{d(on)}$		9		ns
Rise Time		t_r		8		
Turn-Off Delay Time		$t_{d(off)}$		16		
Fall Time		t_f		10		

SOURCE-DRAIN DIODE CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Diode Forward Voltage	$I_S = 3.0\text{ A}, V_{GS} = 0\text{ V}$	V_{SD}			1.6	V
Reverse Recovery Time	$V_{GS} = 0\text{ V}, V_{DD} = 30\text{ V}$ $I_S = 3.0\text{ A}, di/dt = 100\text{ A/μs}$	t_{rr}		265		ns
Reverse Recovery Charge		Q_{rr}		0.9		μC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

5. Pulse Width ≤ 380 μs, Duty Cycle ≤ 2%.

6. Guaranteed by design.

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TYPICAL CHARACTERISTICS

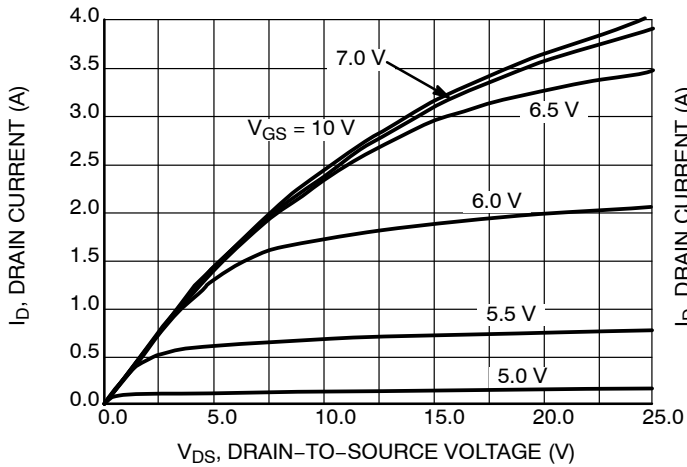


Figure 1. On-Region Characteristics

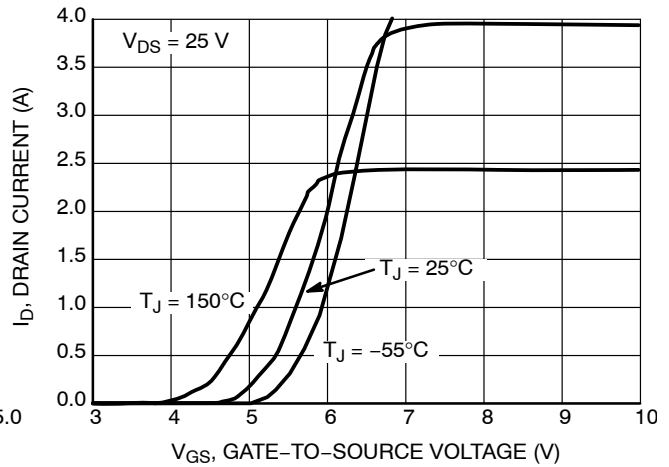


Figure 2. Transfer Characteristics

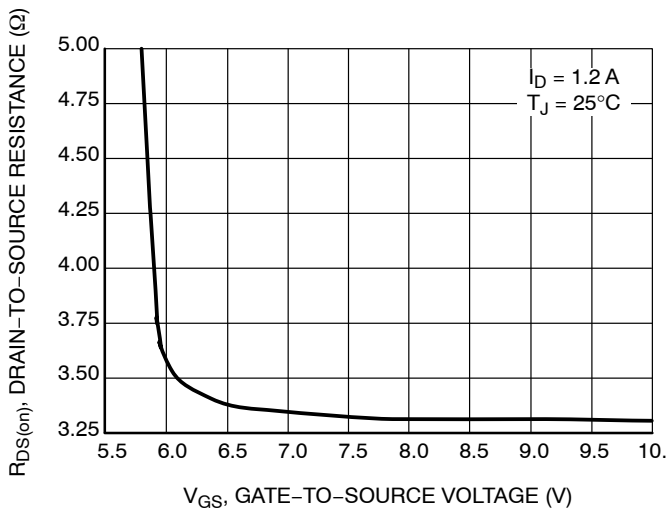


Figure 3. On-Region versus Gate-to-Source Voltage

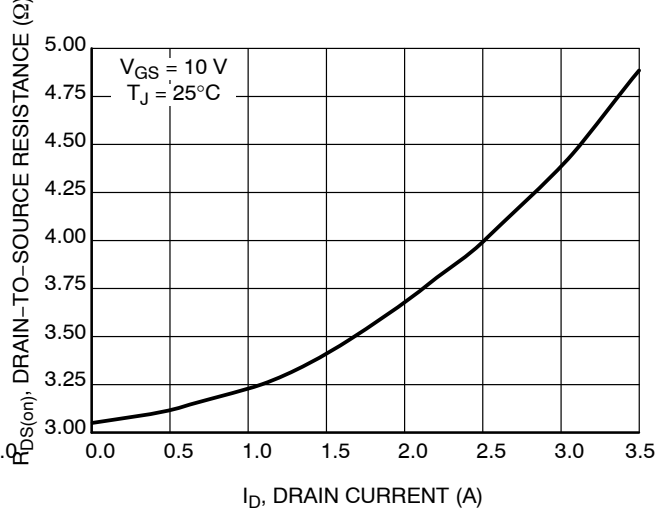


Figure 4. On-Resistance versus Drain Current and Gate Voltage

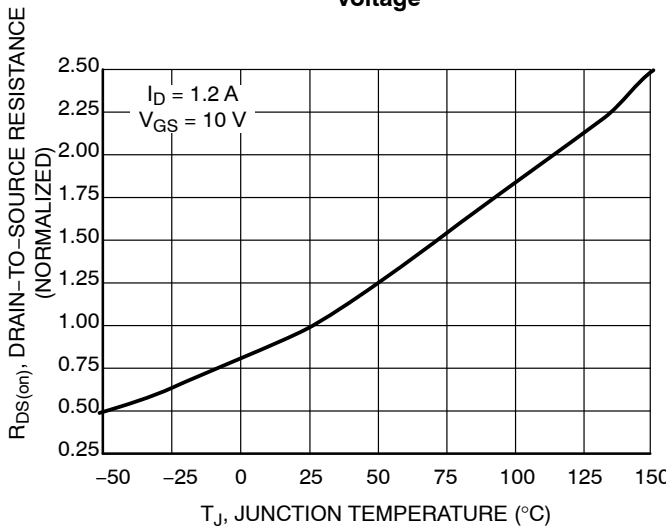


Figure 5. On-Resistance Variation with Temperature

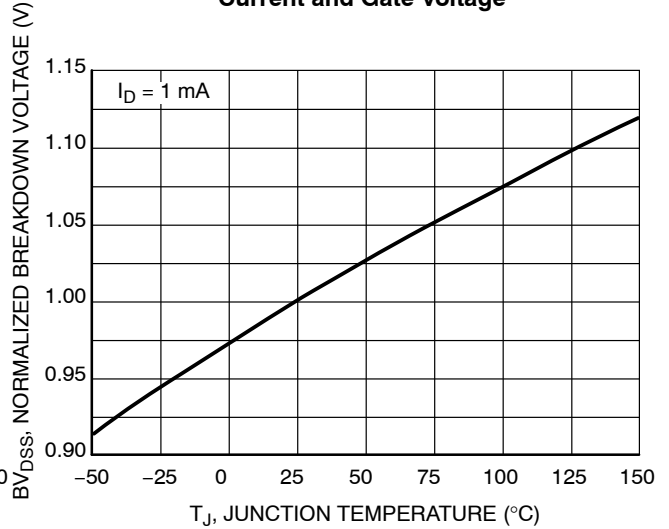


Figure 6. BV_{DSS} Variation with Temperature

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TYPICAL CHARACTERISTICS

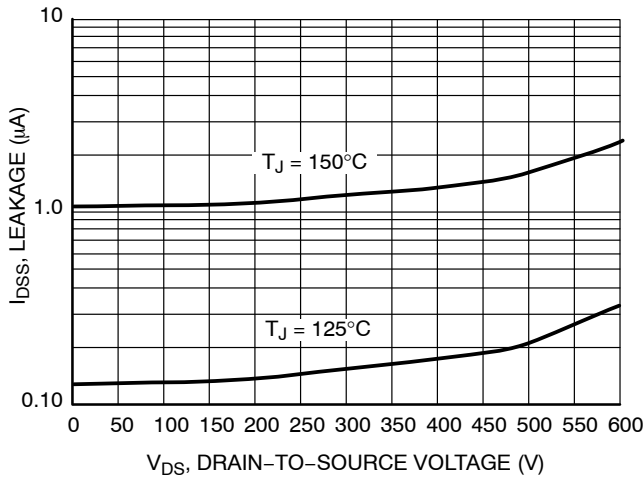


Figure 7. Drain-to-Source Leakage Current versus Voltage

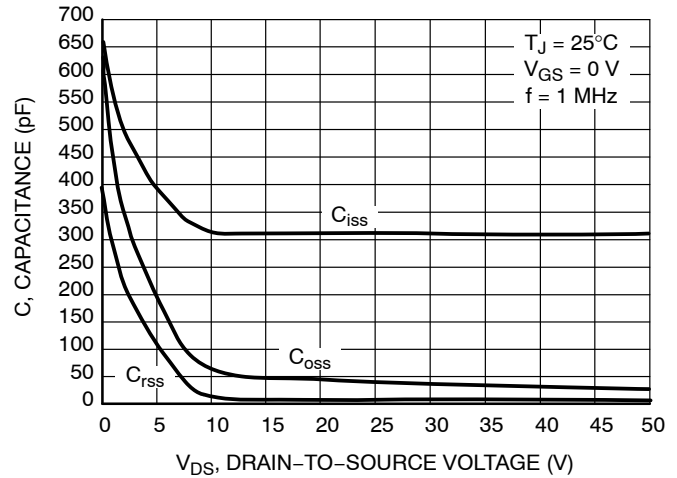


Figure 8. Capacitance Variation

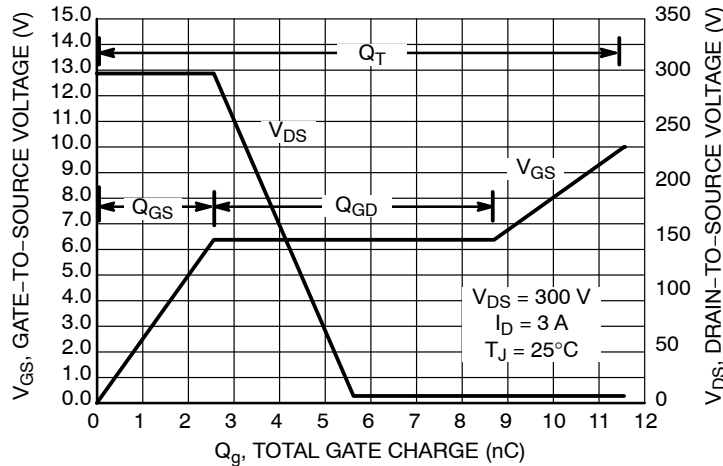


Figure 9. Gate-to-Source Voltage and Drain-to-Source Voltage versus Total Charge

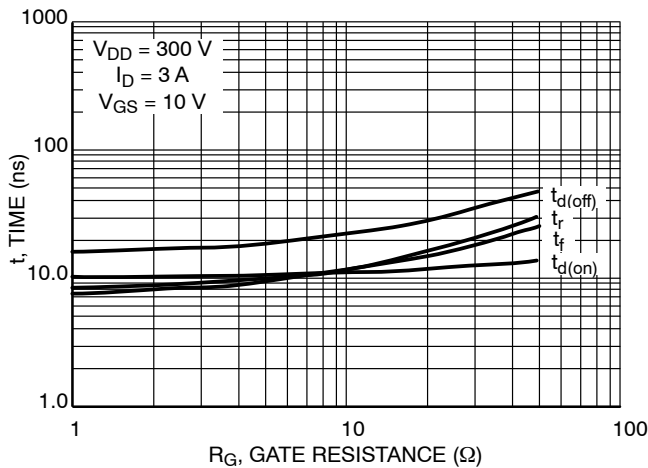


Figure 10. Resistive Switching Time Variation versus Gate Resistance

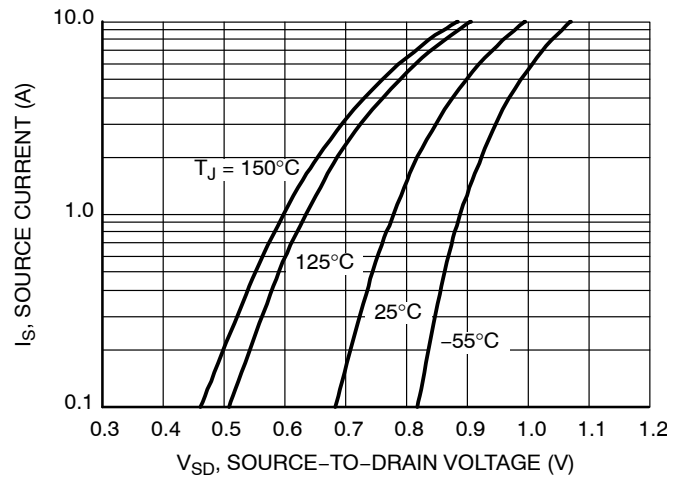


Figure 11. Diode Forward Voltage versus Current

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TYPICAL CHARACTERISTICS

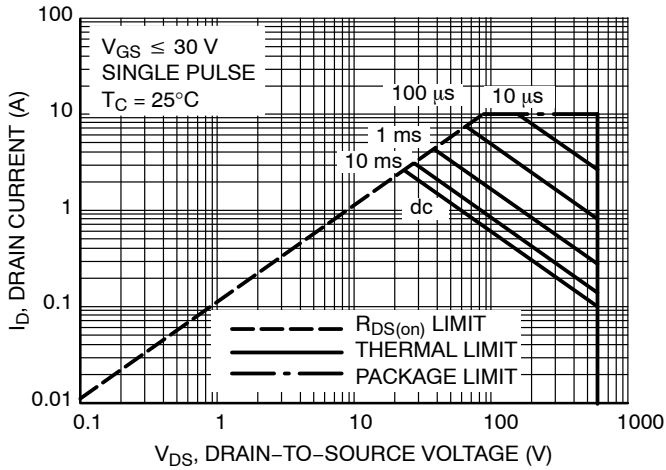


Figure 12. Maximum Rated Forward Biased Safe Operating Area NDD03N60Z

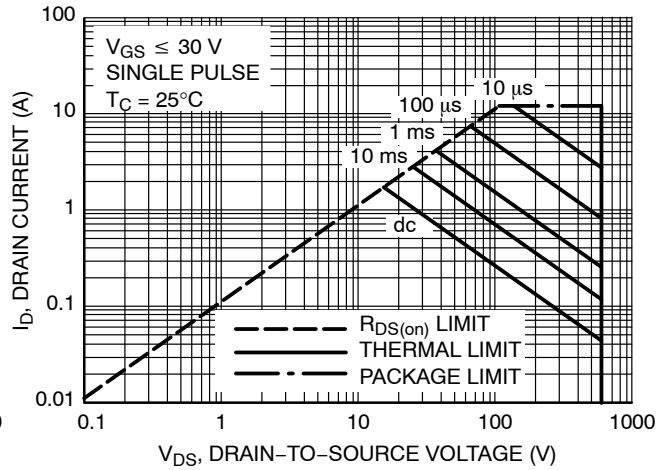


Figure 13. Maximum Rated Forward Biased Safe Operating Area NDF03N60Z

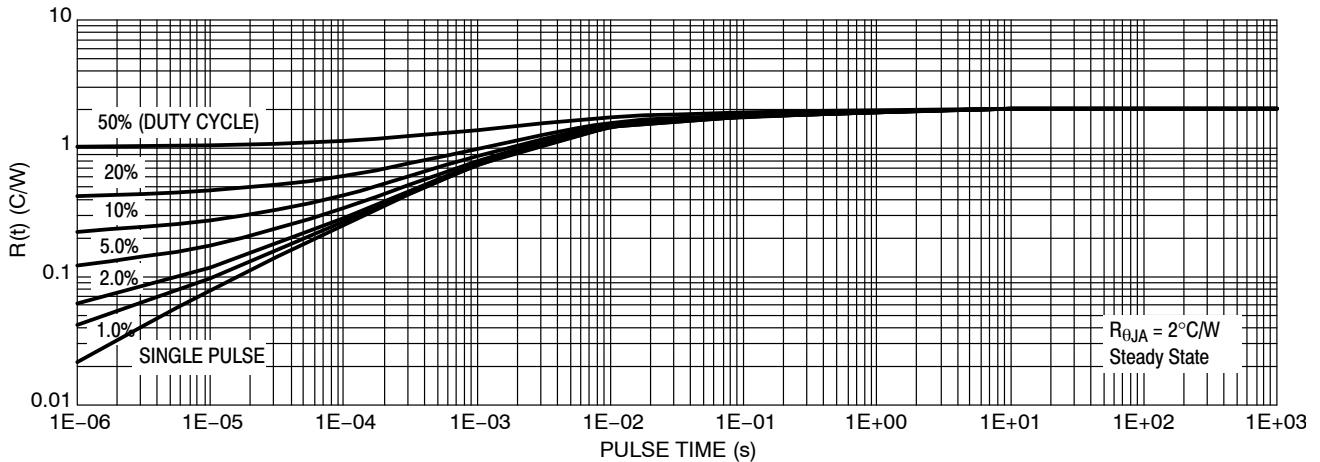


Figure 14. Thermal Impedance (Junction-to-Case) for NDD03N60Z

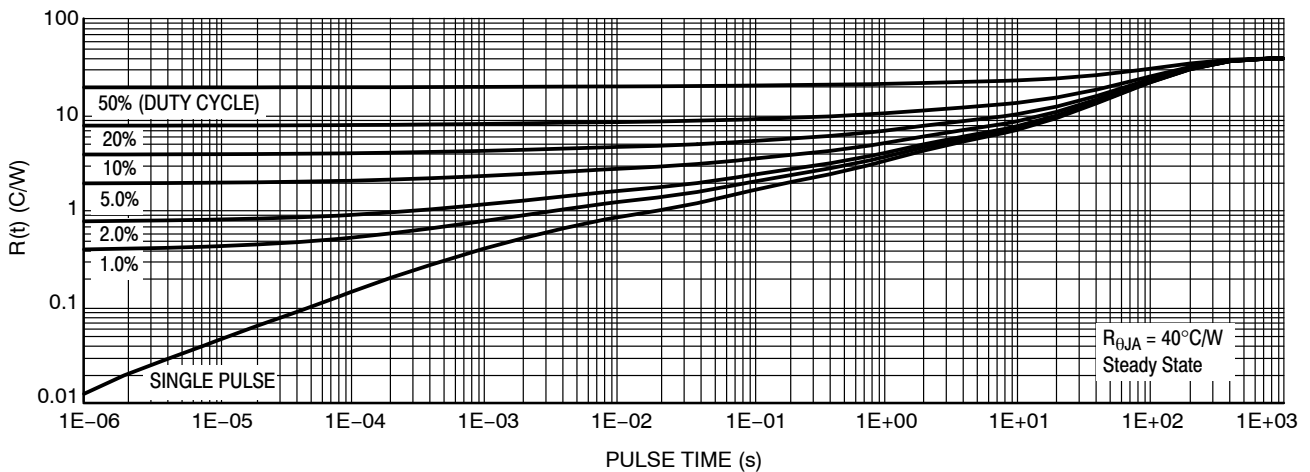


Figure 15. Thermal Impedance (Junction-to-Ambient) for NDD03N60Z

NDF03N60Z, NDD03N60Z

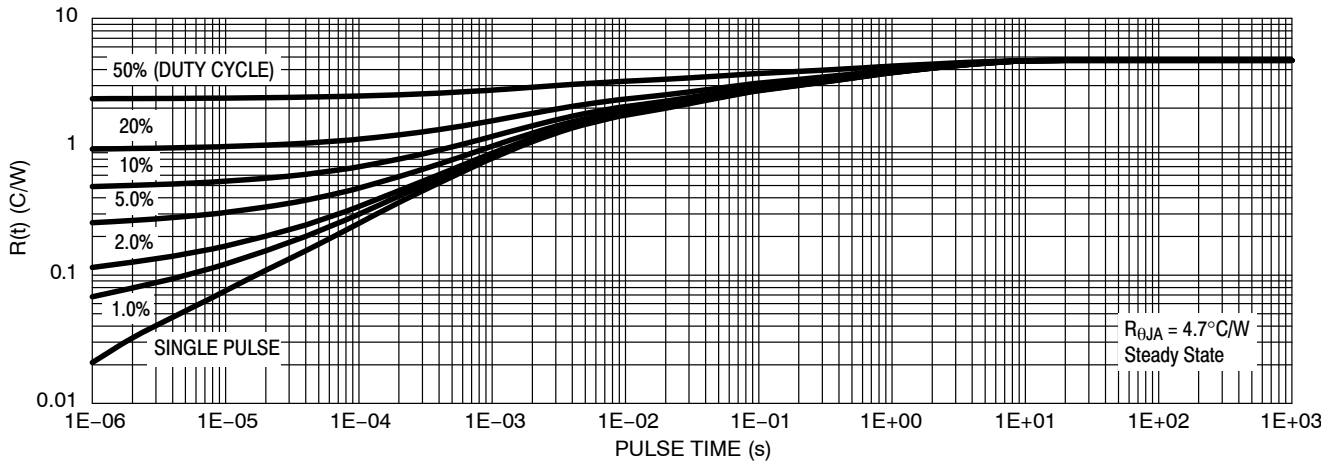


Figure 16. Thermal Impedance (Junction-to-Case) for NDF03N60Z

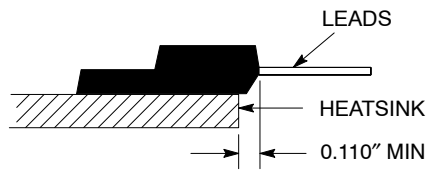


Figure 17. Isolation Test Diagram

Measurement made between leads and heatsink with all leads shorted together.

*For additional mounting information, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

MECHANICAL CASE OUTLINE

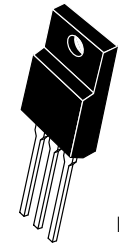
PACKAGE DIMENSIONS

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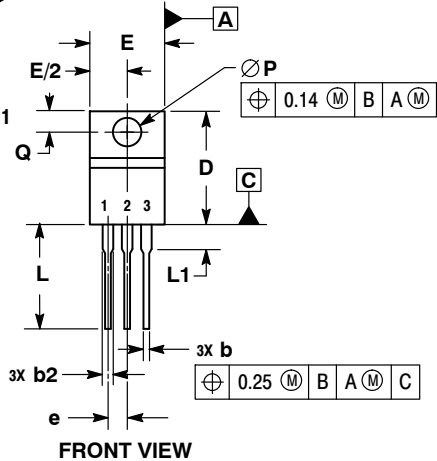


TO-220 FULLPACK, 3-LEAD CASE 221AH ISSUE F

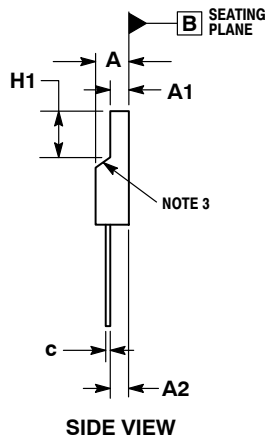
DATE 30 SEP 2014



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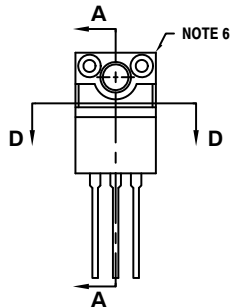
FRONT VIEW



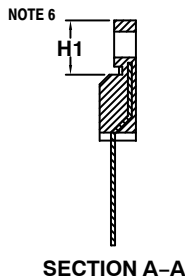
SIDE VIEW



SECTION D-D



ALTERNATE CONSTRUCTION



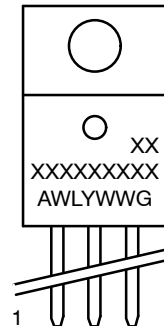
SECTION A-A

NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. CONTOUR UNCONTROLLED IN THIS AREA.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH AND GATE PROTRUSIONS. MOLD FLASH AND GATE PROTRUSIONS NOT TO EXCEED 0.13 PER SIDE. THESE DIMENSIONS ARE TO BE MEASURED AT OUTERMOST EXTREME OF THE PLASTIC BODY.
5. DIMENSION b2 DOES NOT INCLUDE DAMBAR PROTRUSION. LEAD WIDTH INCLUDING PROTRUSION SHALL NOT EXCEED 2.00.
6. CONTOURS AND FEATURES OF THE MOLDED PACKAGE BODY MAY VARY WITHIN THE ENVELOPE DEFINED BY DIMENSIONS A1 AND H1 FOR MANUFACTURING PURPOSES.

MILLIMETERS		
DIM	MIN	MAX
A	4.30	4.70
A1	2.50	2.90
A2	2.50	2.90
b	0.54	0.84
b2	1.10	1.40
c	0.49	0.79
D	14.70	15.30
E	9.70	10.30
e	2.54 BSC	
H1	6.60	7.10
L	12.50	14.73
L1	---	2.80
P	3.00	3.40
Q	2.80	3.20

GENERIC MARKING DIAGRAM*



- A = Assembly Location
- WL = Wafer Lot
- Y = Year
- WW = Work Week
- G = Pb-Free Package

STYLE 1:

1. MAIN TERMINAL 1
2. MAIN TERMINAL 2
3. GATE

STYLE 2:

1. CATHODE
2. ANODE
3. GATE

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present.

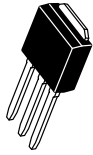
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MECHANICAL CASE OUTLINE

PACKAGE DIMENSIONS

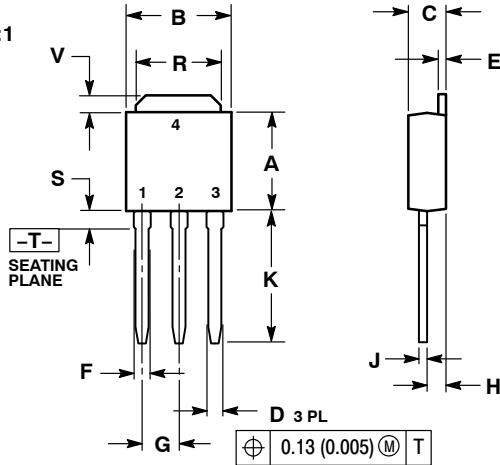
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IPAK CASE 369D-01 ISSUE C

DATE 15 DEC 2010

SCALE 1:1



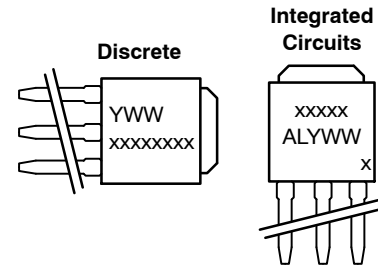
NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.235	0.245	5.97	6.35
B	0.250	0.265	6.35	6.73
C	0.086	0.094	2.19	2.38
D	0.027	0.035	0.69	0.88
E	0.018	0.023	0.46	0.58
F	0.037	0.045	0.94	1.14
G	0.090	BSC	2.29	BSC
H	0.034	0.040	0.87	1.01
J	0.018	0.023	0.46	0.58
K	0.350	0.380	8.89	9.65
R	0.180	0.215	4.45	5.45
S	0.025	0.040	0.63	1.01
V	0.035	0.050	0.89	1.27
Z	0.155	---	3.93	---

- | | | | |
|--|---|--|--|
| <p>STYLE 1:
PIN 1. BASE
2. COLLECTOR
3. EMITTER
4. COLLECTOR</p> | <p>STYLE 2:
PIN 1. GATE
2. DRAIN
3. SOURCE
4. DRAIN</p> | <p>STYLE 3:
PIN 1. ANODE
2. CATHODE
3. ANODE
4. CATHODE</p> | <p>STYLE 4:
PIN 1. CATHODE
2. ANODE
3. GATE
4. ANODE</p> |
| <p>STYLE 5:
PIN 1. GATE
2. ANODE
3. CATHODE
4. ANODE</p> | <p>STYLE 6:
PIN 1. MT1
2. MT2
3. GATE
4. MT2</p> | <p>STYLE 7:
PIN 1. GATE
2. COLLECTOR
3. EMITTER
4. COLLECTOR</p> | |

MARKING DIAGRAMS



- xxxxxxxx = Device Code
- A = Assembly Location
- IL = Wafer Lot
- Y = Year
- WW = Work Week

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